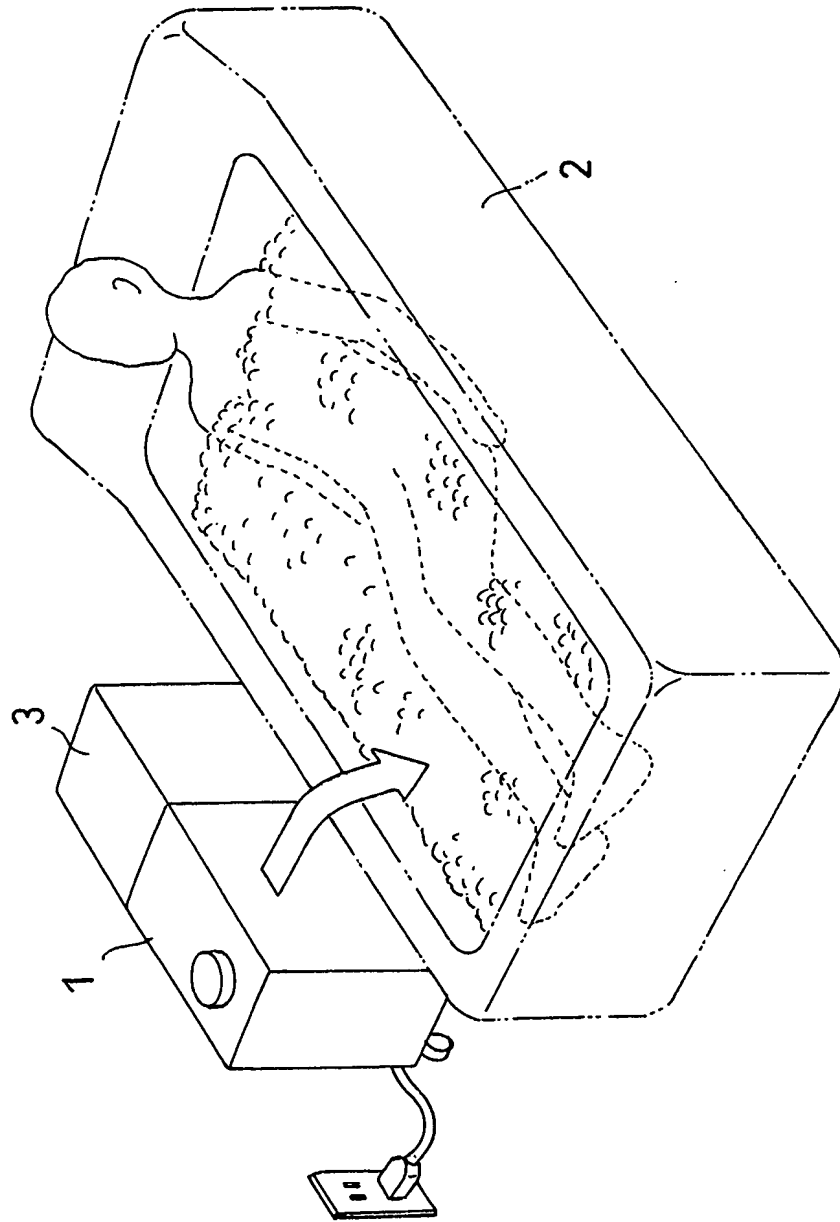


FIG. 1



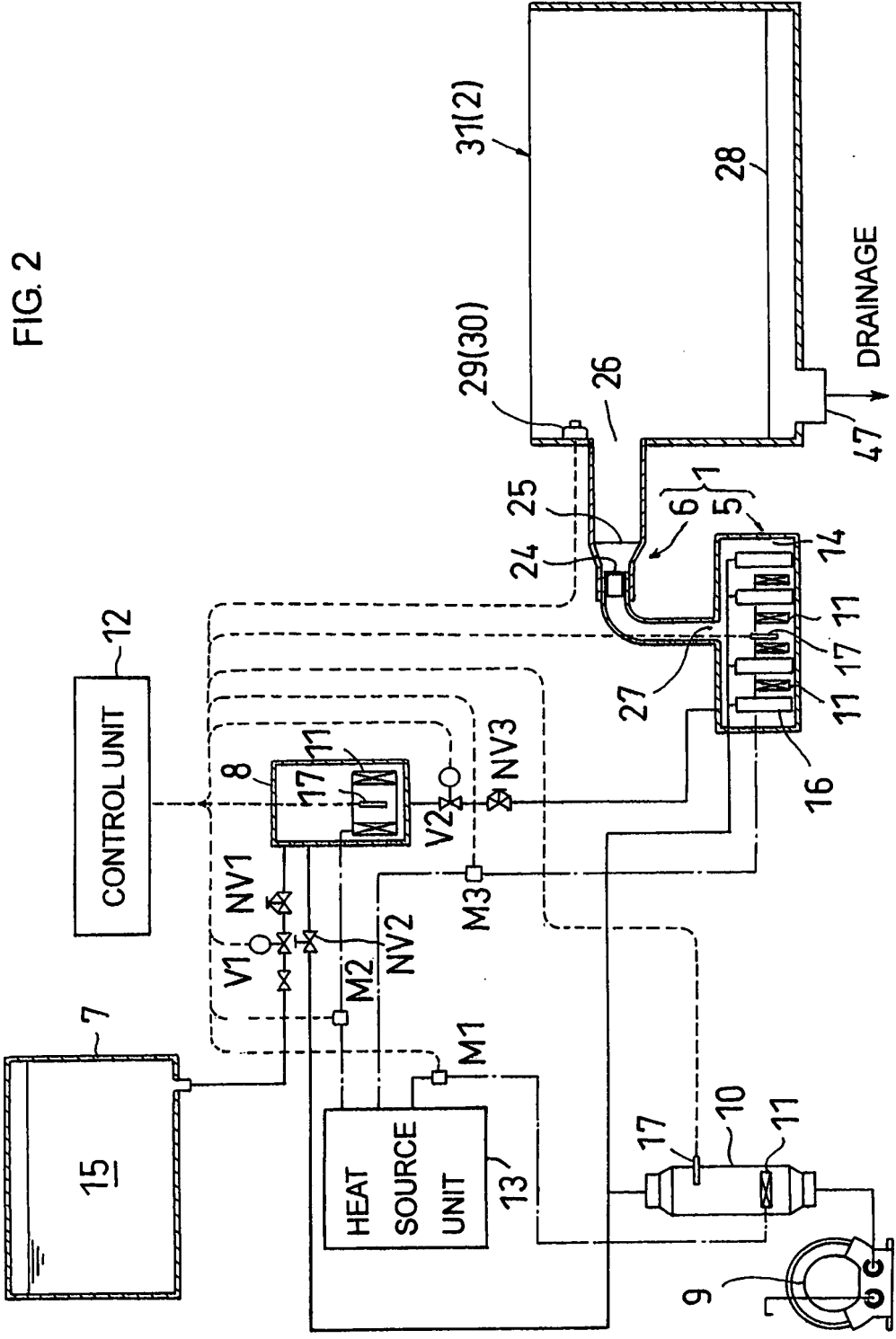


FIG. 2

This diagram shows a cross-sectional view of a semiconductor device. A trench (15) is formed in a substrate (5). The trench is filled with a conductive material (16). A conductive plug (18) is formed in the trench, extending from the bottom to the top. The plug is surrounded by a dielectric material (17). The top surface of the plug is exposed. The device is labeled with various reference numerals: 5, 15, 16, 17, 18, 21, 23, 27, and 29.

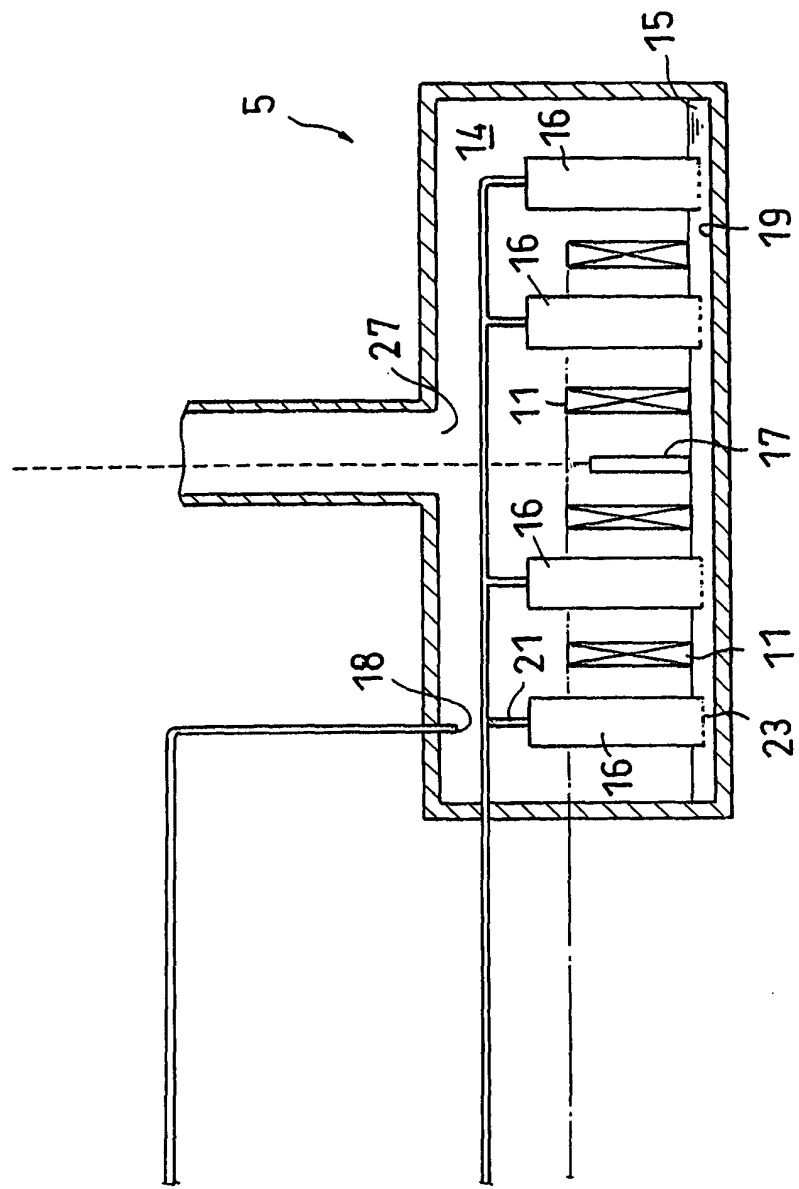


FIG. 4

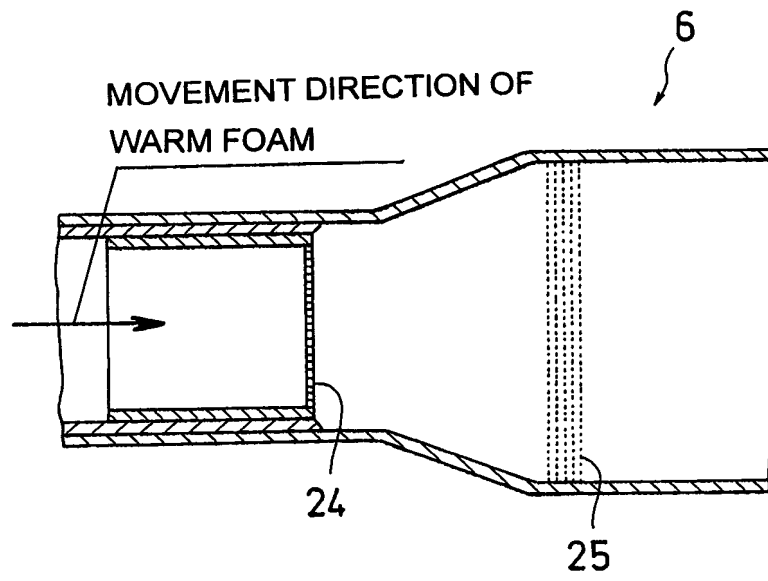


FIG. 5

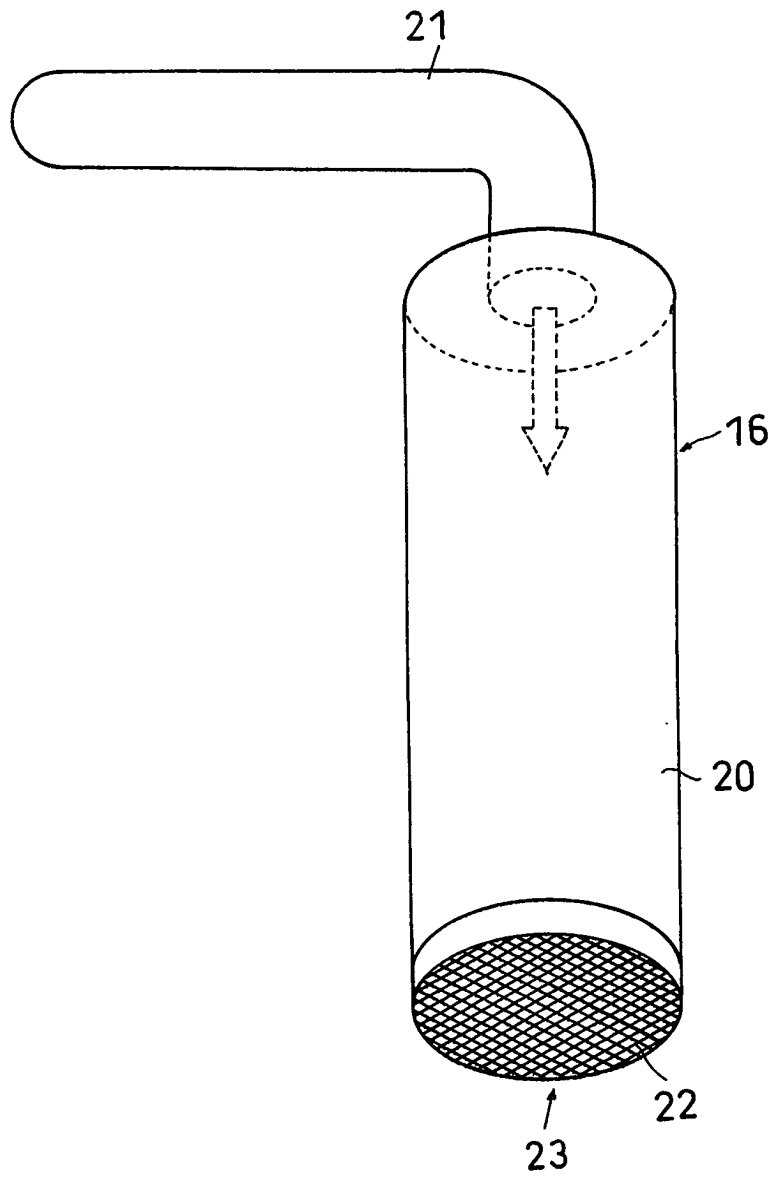


FIG. 6 A

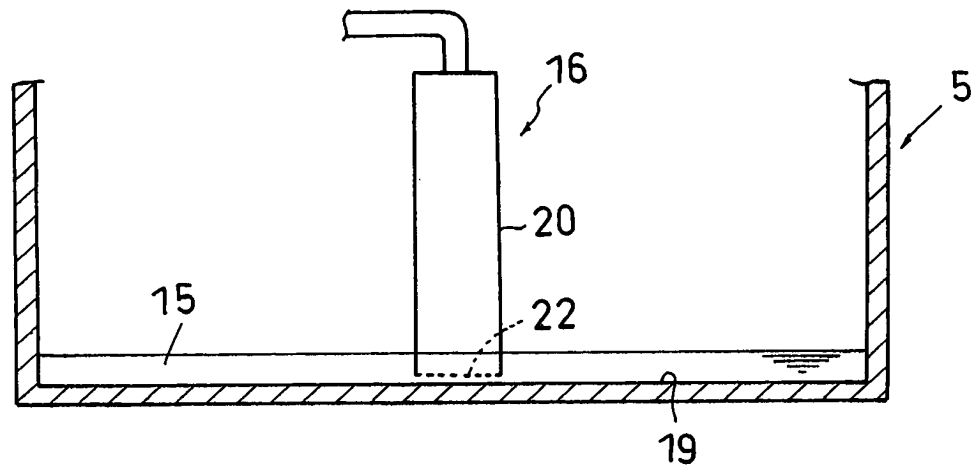


FIG. 6 B

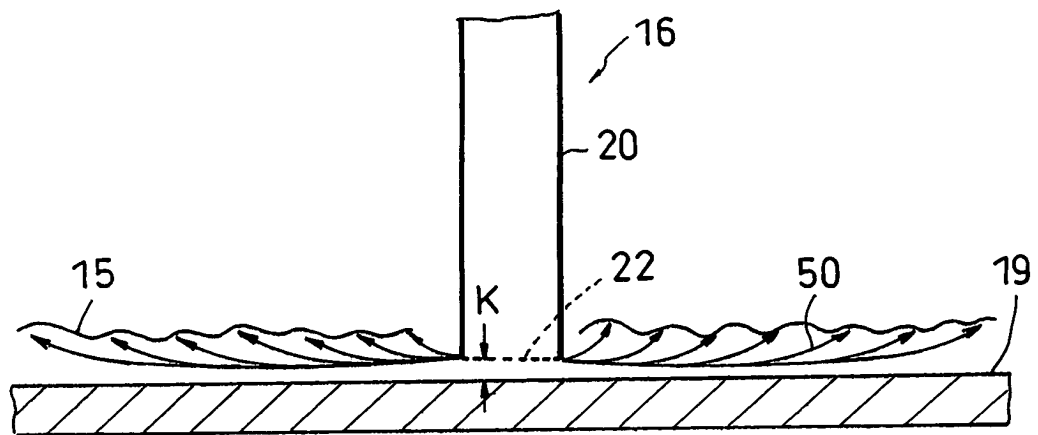


FIG. 7

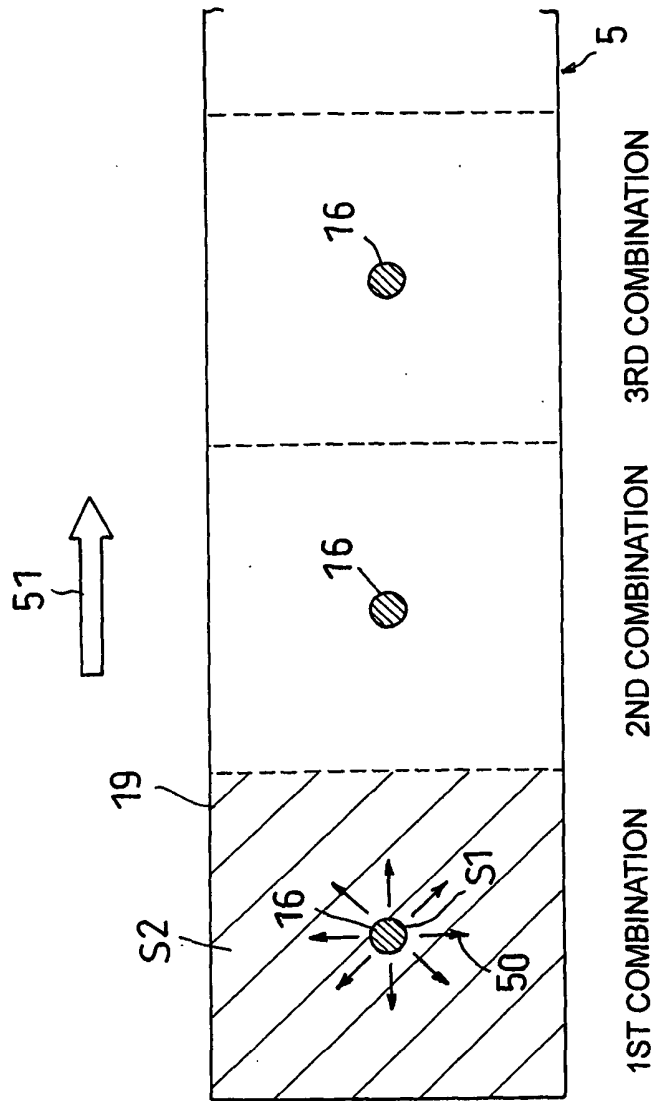


FIG. 8A

2-LAYER NETS

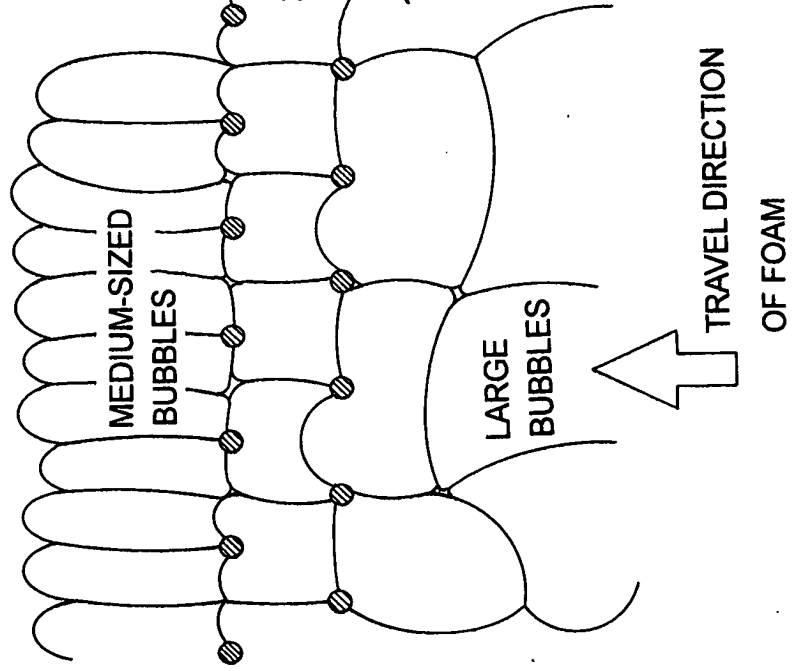


FIG. 8B

4-LAYER NETS

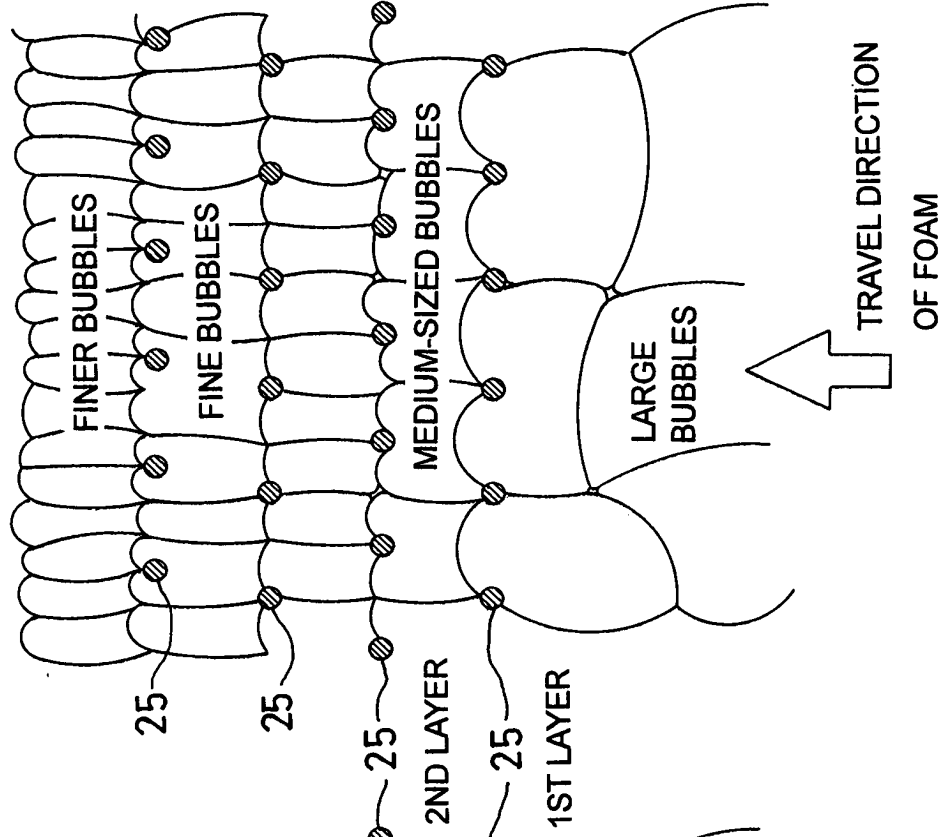


FIG. 9

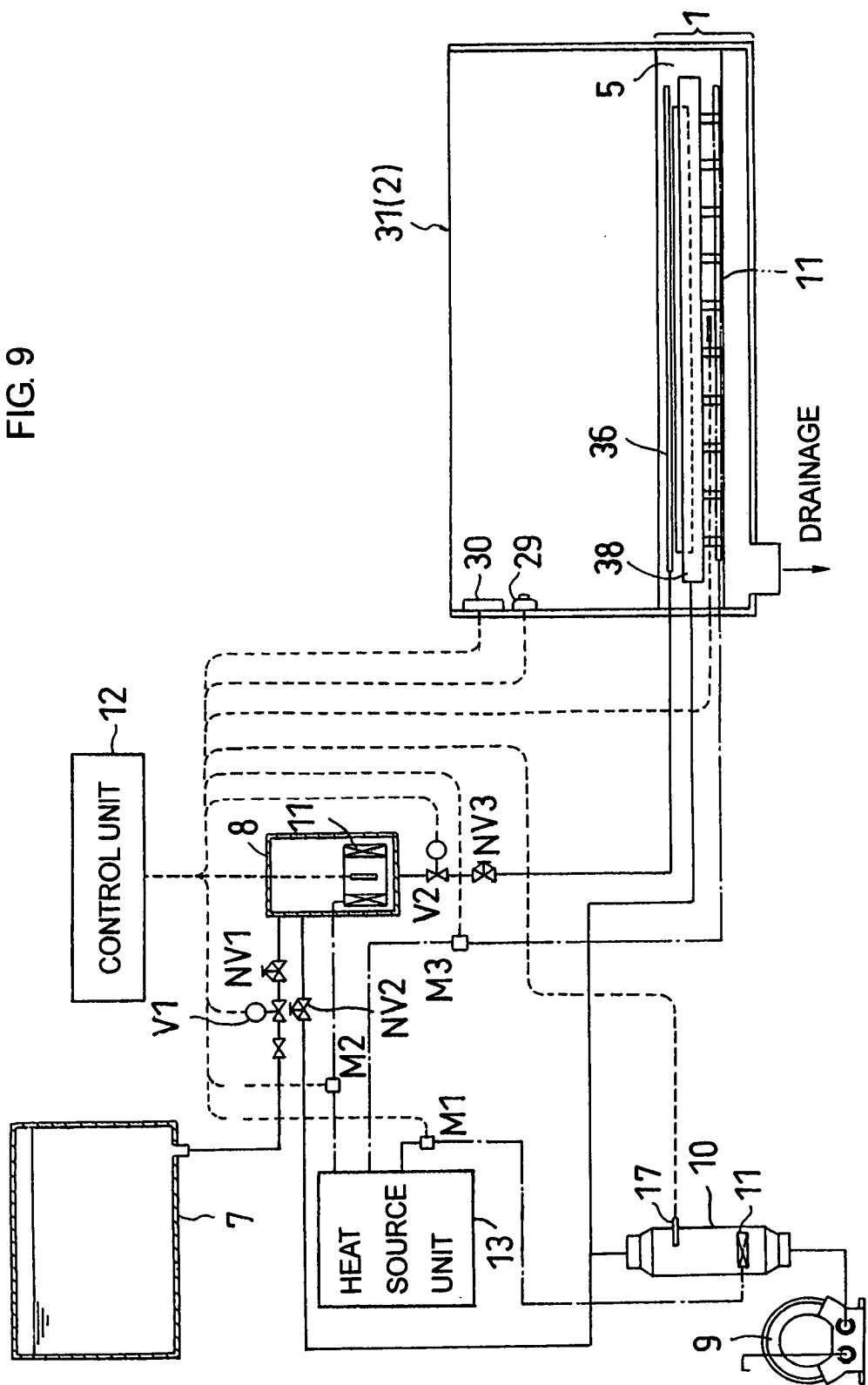


FIG. 10

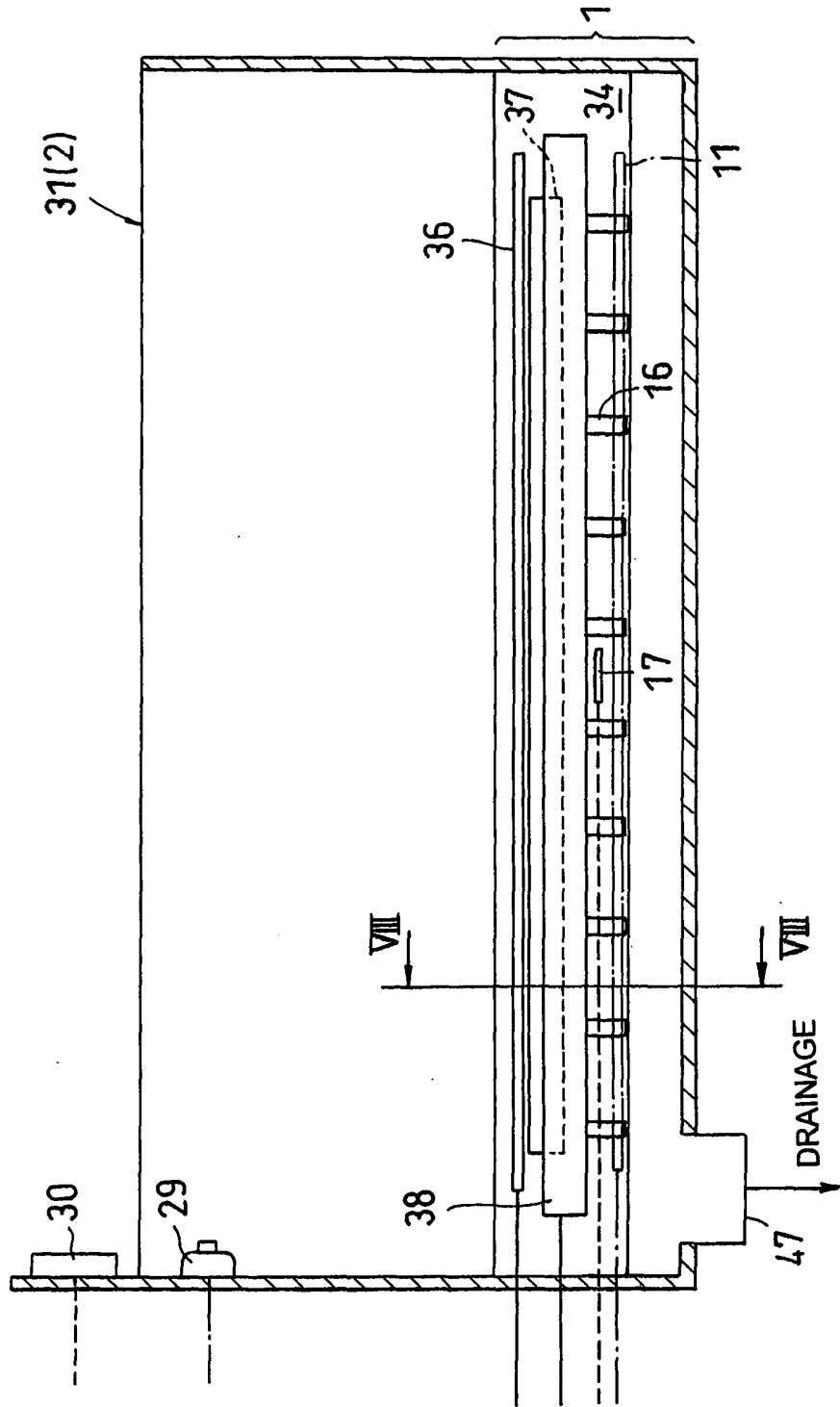


FIG. 11

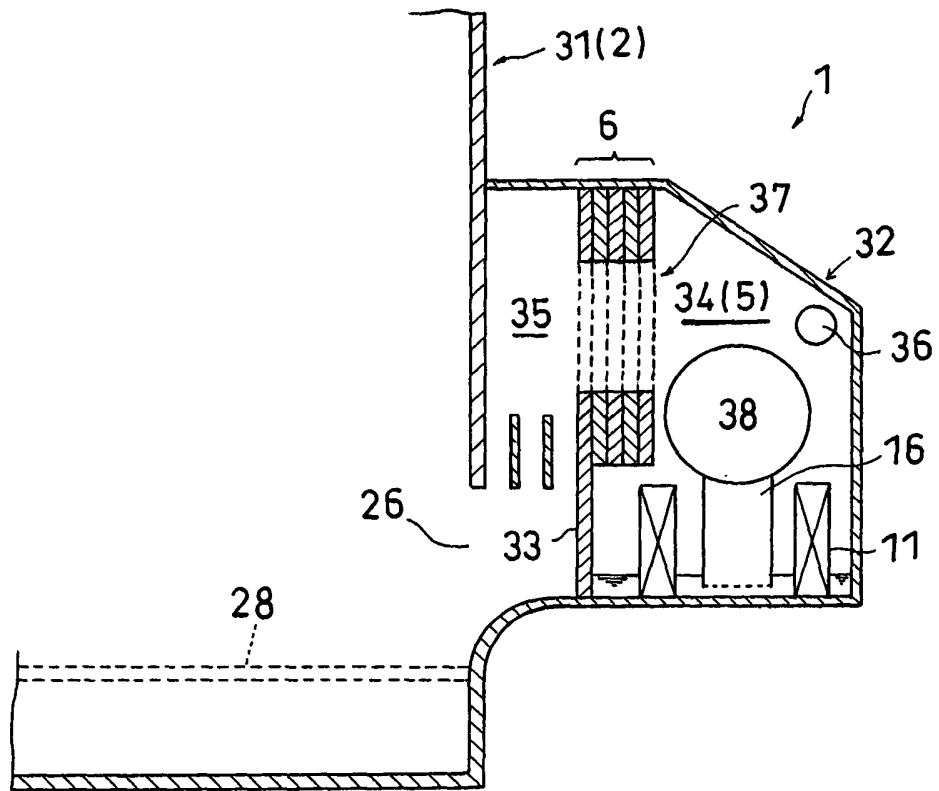
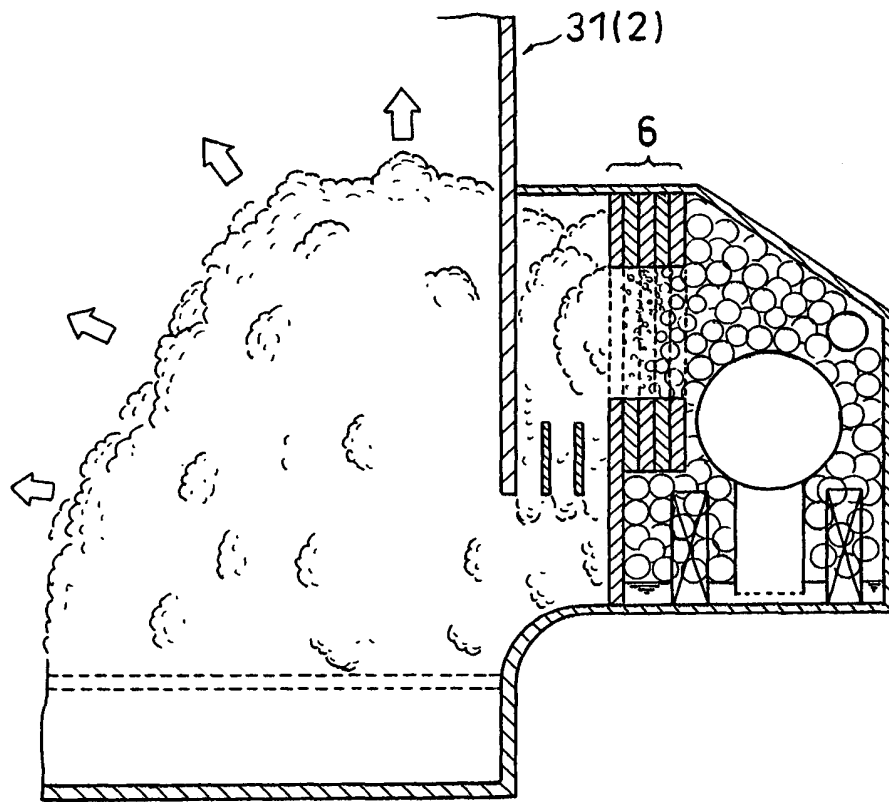


FIG. 12



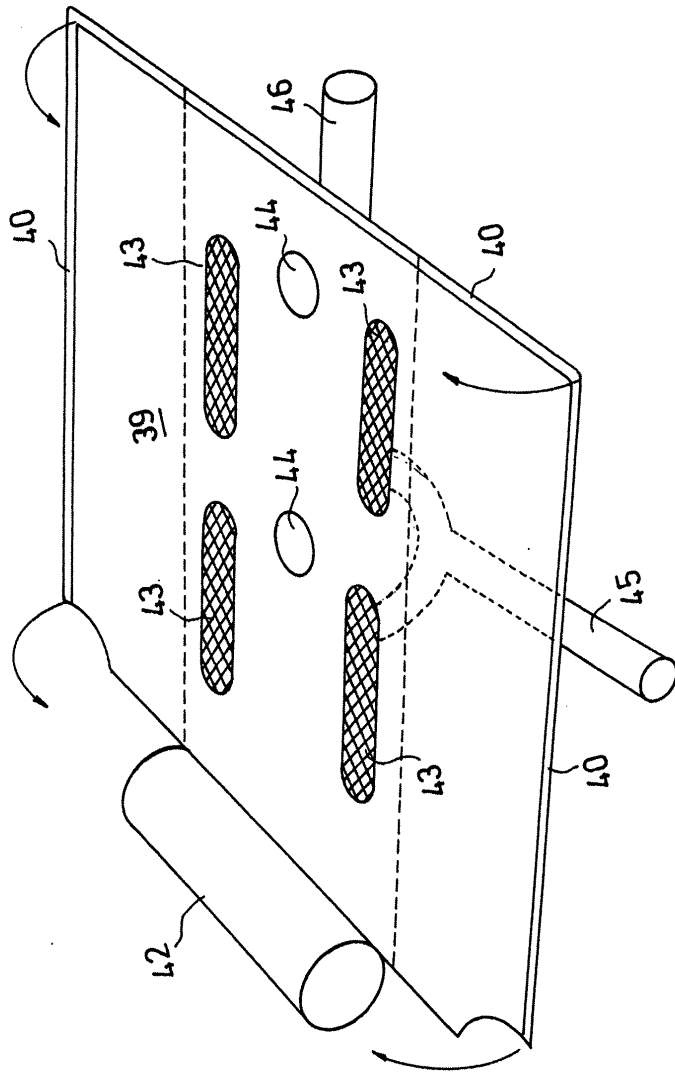


FIG. 14

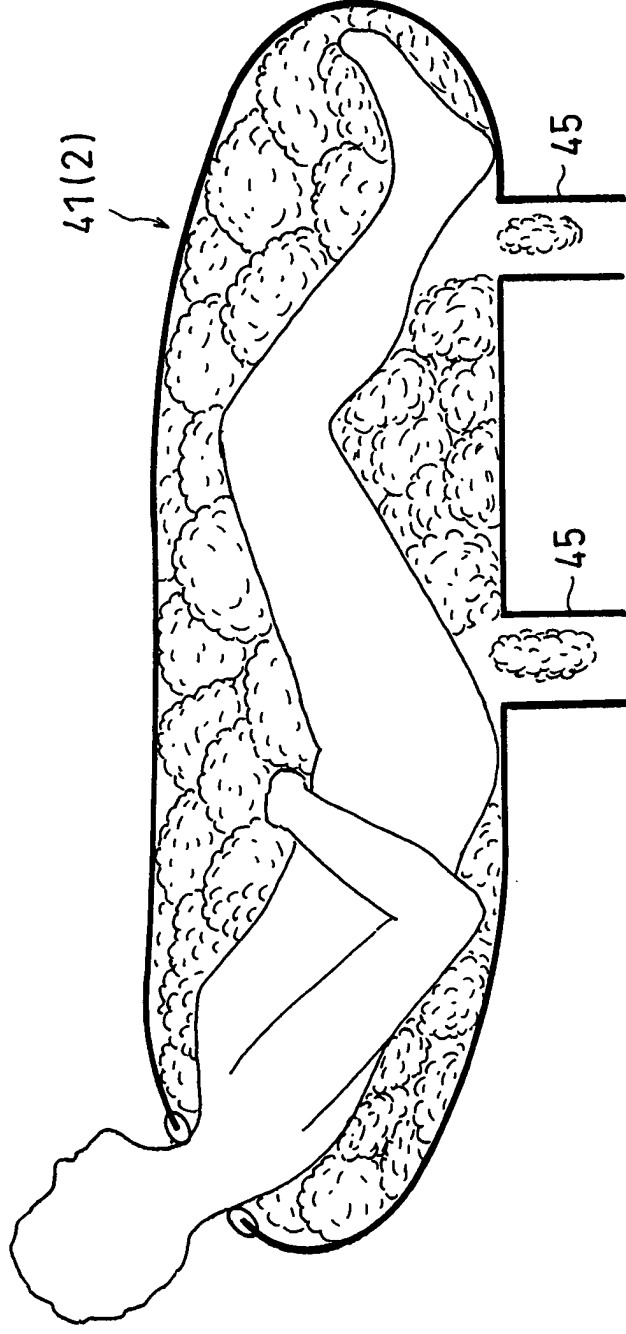
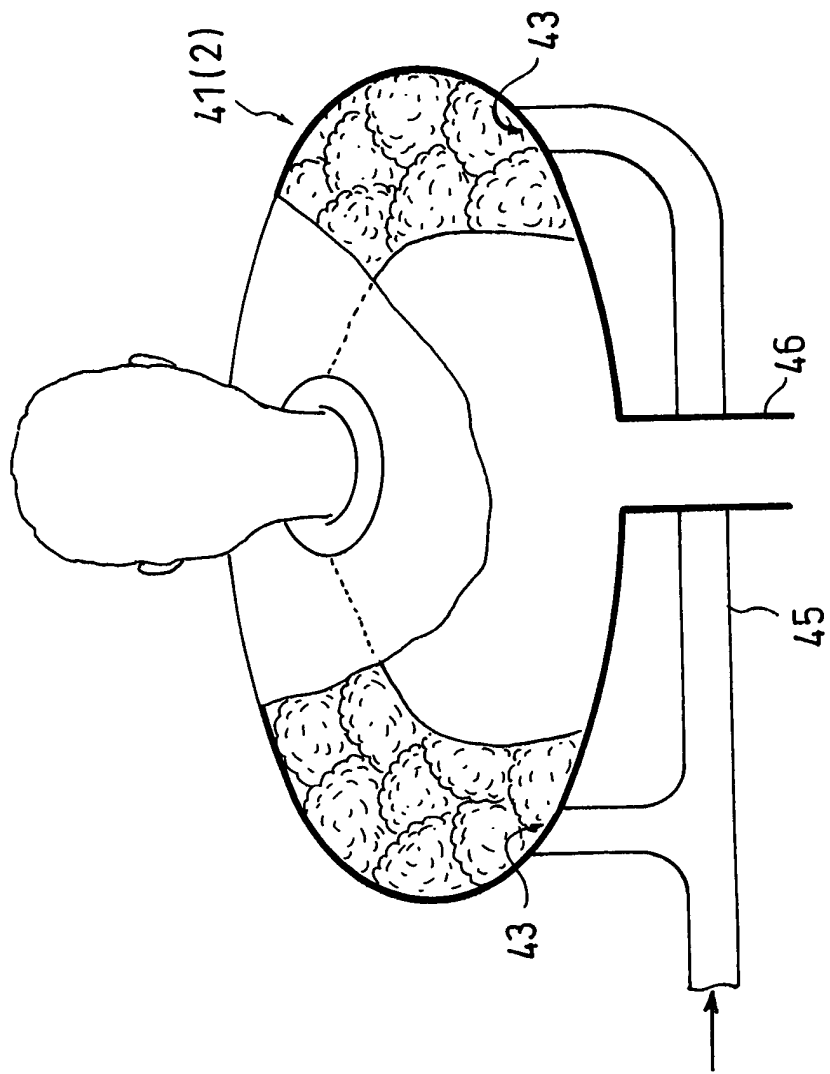


FIG. 15



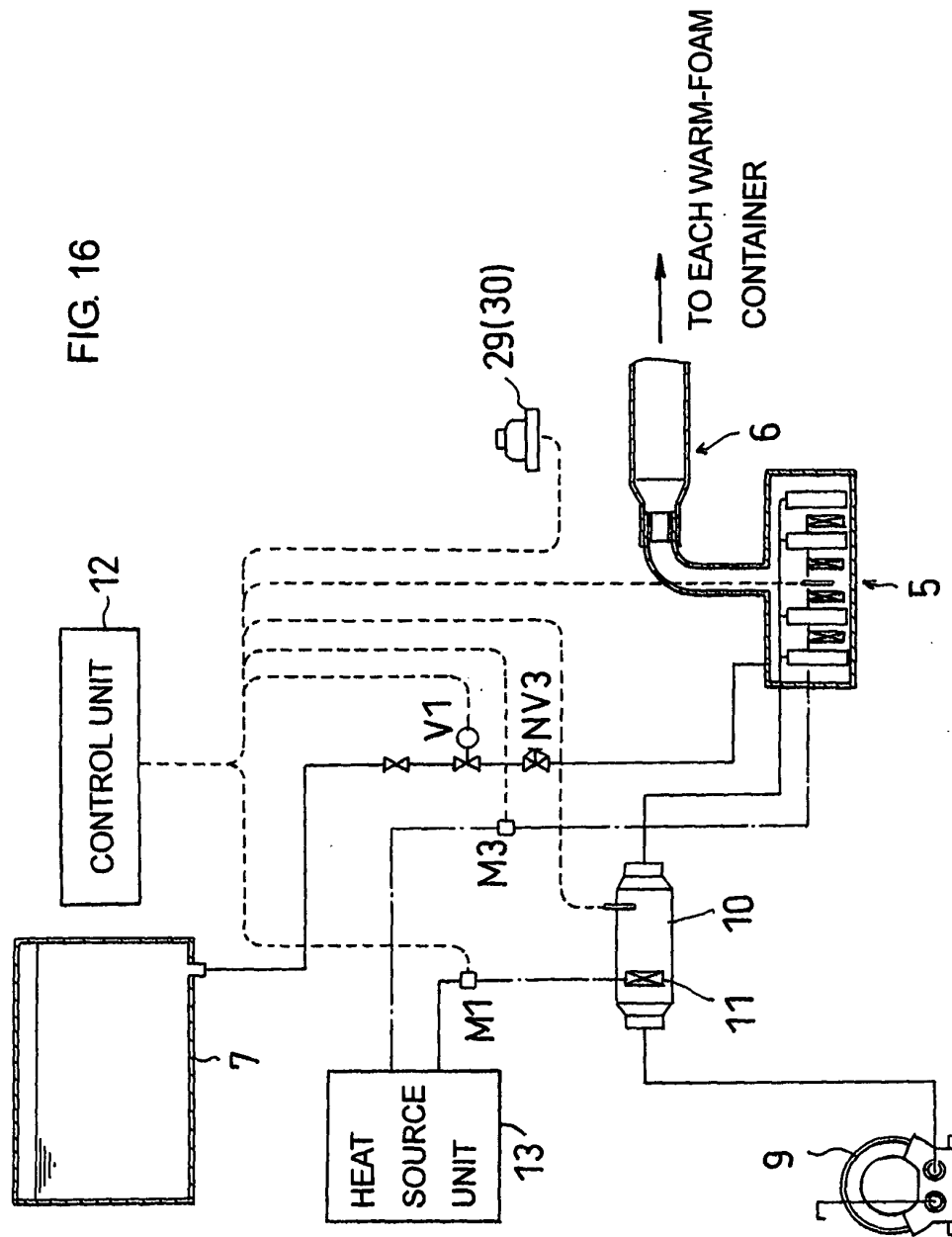


FIG. 17B

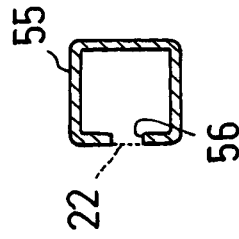


FIG. 17D

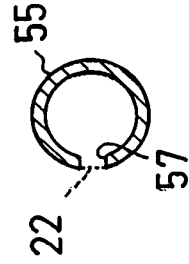


FIG. 17F

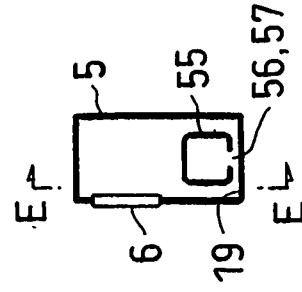


FIG. 17A

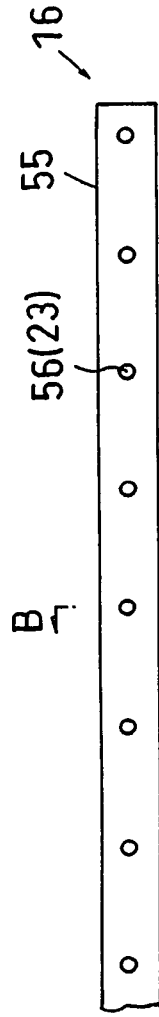


FIG. 17C

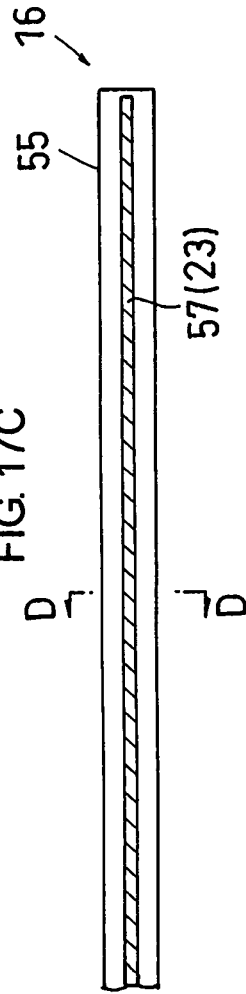


FIG. 17E

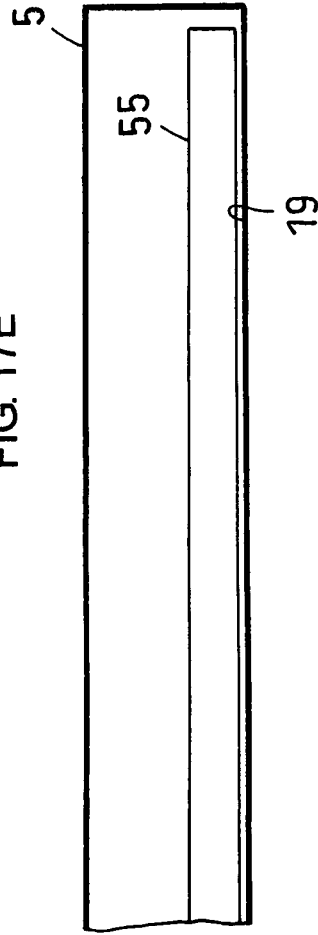


FIG. 18A

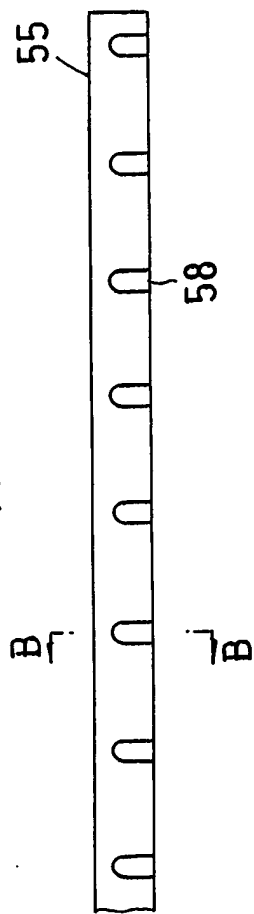


FIG. 18C

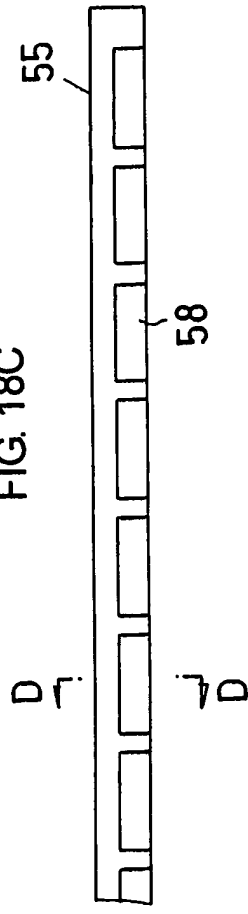


FIG. 18E

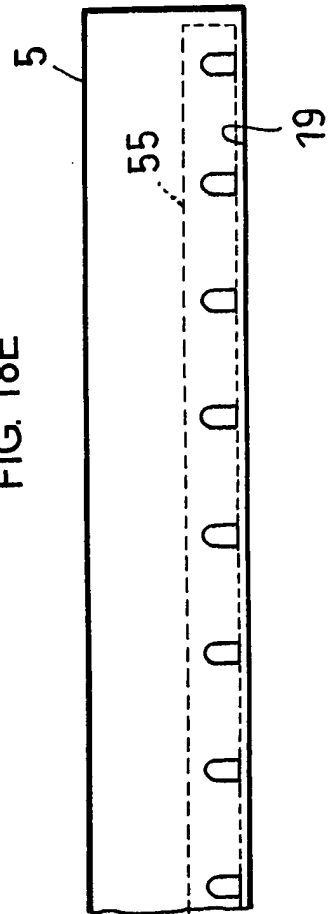


FIG. 18B

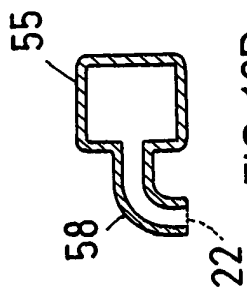


FIG. 18D

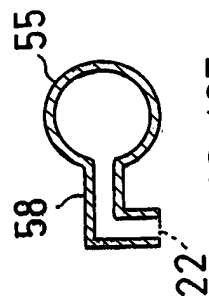


FIG. 18F

